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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	· ·
Number of Logic Elements/Cells	·
Total RAM Bits	110592
Number of I/O	97
Number of Gates	600000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	144-LBGA
Supplier Device Package	144-FPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p600l-fgg144

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

- · The device is reset upon exiting Flash*Freeze mode or internal state saving is not required.
- State saving is required, but data and clock management is performed external to the FPGA. In other words, incoming data is externally guaranteed and held valid prior to entering Flash*Freeze mode.

Type 2 Flash*Freeze mode is ideally suited for applications with the following design criteria:

- Entering Flash*Freeze mode is dependent on an internal or external signal in addition to the external FF pin.
- State saving is required and incoming data is not externally guaranteed valid.
- The designer wants to use his/her own Flash*Freeze management IP for clock and data management.
- The designer wants to use his/her own Flash*Freeze management logic for clock and data management.
- Internal housekeeping is required prior to entering Flash*Freeze mode. Housekeeping activities
 may include loading data to SRAM, system shutdown, completion of current task, or ensuring
 valid Flash*Freeze pin assertion.

There is no downside to type 2 mode, and Microsemi's Flash*Freeze management IP offers a very low tile count clock and data management solution. Microsemi's recommendation for most designs is to use type 2 Flash*Freeze mode with Flash*Freeze management IP.

Design Solutions

Clocks

- Microsemi recommends using a completely synchronous design in Type 2 mode with Flash*Freeze management IP cleanly gating all internal and external clocks. This will prevent narrow pulses upon entrance and exit from Flash*Freeze mode (Figure 2-5 on page 30).
- Upon entering Flash*Freeze mode, external clocks become tied off High, internal to the clock pin (unless hold state is used on IGLOO nano or IGLOO PLUS), and PLLs are turned off. Any clock that is externally Low will realize a Low to High transition internal to the device while entering Flash*Freeze. If clocks will float during Flash*Freeze mode, Microsemi recommends using the weak pull-up feature. If clocks will continue to drive the device during Flash*Freeze mode, the clock gating (filter) available in Flash*Freeze management IP can help to filter unwanted narrow clock pulses upon Flash*Freeze mode entry and exit.
- Clocks may continue to drive FPGA pins while the device is in Flash*Freeze mode, with virtually
 no power consumption. The weak pull-up/-down configuration will result in unnecessary power
 consumption if used in this scenario.
- Floating clocks can cause totem pole currents on the input I/O circuitry when the device is in
 active mode. If clocks are externally gated prior to entering Flash*Freeze mode, Microsemi
 recommends gating them to a known value (preferably '1', to avoid a possible narrow pulse upon
 Flash*Freeze mode exit), and not leaving them floating. However, during Flash*Freeze mode, all
 inputs and clocks are internally tied off to prevent totem pole currents, so they can be left floating.
- Upon exiting Flash*Freeze mode, the design must allow maximum acquisition time for the PLL to acquire the lock signal, and for a PLL clock to become active. If a PLL output clock is used as the primary clock for Flash*Freeze management IP, it is important to note that the clock gating circuit will only release other clocks after the primary PLL output clock becomes available.

Spine Architecture

The low power flash device architecture allows the VersaNet global networks to be segmented. Each of these networks contains spines (the vertical branches of the global network tree) and ribs that can reach all the VersaTiles inside its region. The nine spines available in a vertical column reside in global networks with two separate regions of scope: the quadrant global network, which has three spines, and the chip (main) global network, which has six spines. Note that the number of quadrant globals and globals/spines per tree varies depending on the specific device. Refer to Table 3-4 for the clocking resources available for each device. The spines are the vertical branches of the global network tree, shown in Figure 3-3 on page 50. Each spine in a vertical column of a chip (main) global network is further divided into two spine segments of equal lengths: one in the top and one in the bottom half of the die (except in 10 k through 30 k gate devices).

Top and bottom spine segments radiating from the center of a device have the same height. However, just as in the ProASIC^{PLUS®} family, signals assigned only to the top and bottom spine cannot access the middle two rows of the die. The spines for quadrant clock networks do not cross the middle of the die and cannot access the middle two rows of the architecture.

Each spine and its associated ribs cover a certain area of the device (the "scope" of the spine; see Figure 3-3 on page 50). Each spine is accessed by the dedicated global network MUX tree architecture, which defines how a particular spine is driven—either by the signal on the global network from a CCC, for example, or by another net defined by the user. Details of the chip (main) global network spine-selection MUX are presented in Figure 3-8 on page 60. The spine drivers for each spine are located in the middle of the die.

Quadrant spines can be driven from user I/Os or an internal signal from the north and south sides of the die. The ability to drive spines in the quadrant global networks can have a significant effect on system performance for high-fanout inputs to a design. Access to the top quadrant spine regions is from the top of the die, and access to the bottom quadrant spine regions is from the bottom of the die. The A3PE3000 device has 28 clock trees and each tree has nine spines; this flexible global network architecture enables users to map up to 252 different internal/external clocks in an A3PE3000 device.

			Orrections		Globals/	Total			Rows
ProASIC3/ ProASIC3L Devices	IGLOO Devices	Chip Globals	Globals (4×3)	Clock Trees	per Tree	per Device	in Each Tree	Total VersaTiles	Each Spine
A3PN010	AGLN010	4	0	1	0	0	260	260	4
A3PN015	AGLN015	4	0	1	0	0	384	384	6
A3PN020	AGLN020	4	0	1	0	0	520	520	6
A3PN060	AGLN060	6	12	4	9	36	384	1,536	12
A3PN125	AGLN125	6	12	8	9	72	384	3,072	12
A3PN250	AGLN250	6	12	8	9	72	768	6,144	24
A3P015	AGL015	6	0	1	9	9	384	384	12
A3P030	AGL030	6	0	2	9	18	384	768	12
A3P060	AGL060	6	12	4	9	36	384	1,536	12
A3P125	AGL125	6	12	8	9	72	384	3,072	12
A3P250/L	AGL250	6	12	8	9	72	768	6,144	24
A3P400	AGL400	6	12	12	9	108	768	9,216	24
A3P600/L	AGL600	6	12	12	9	108	1,152	13,824	36
A3P1000/L	AGL1000	6	12	16	9	144	1,536	24,576	48
A3PE600/L	AGLE600	6	12	12	9	108	1,120	13,440	35
A3PE1500		6	12	20	9	180	1,888	37,760	59
A3PE3000/L	AGLE3000	6	12	28	9	252	2,656	74,368	83

Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices

Each global buffer, as well as the PLL reference clock, can be driven from one of the following:

- 3 dedicated single-ended I/Os using a hardwired connection
- 2 dedicated differential I/Os using a hardwired connection (not applicable for IGLOO nano and ProASIC3 nano devices)
- The FPGA core

Since the architecture of the devices varies as size increases, the following list details I/O types supported for globals:

IGLOO and ProASIC3

- LVDS-based clock sources are available only on 250 k gate devices and above (IGLOO nano and ProASIC3 nano devices do not support differential inputs).
- 60 k and 125 k gate devices support single-ended clock sources only.
- 15 k and 30 k gate devices support these inputs for CCC only and do not contain a PLL.
- nano devices:
 - 10 k, 15 k, and 20 k devices do not contain PLLs in the CCCs, and support only CLKBUF and CLKINT.
 - 60 k, 125 k, and 250 k devices support one PLL in the middle left CCC position. In the absence of the PLL, this CCC can be used by CLKBUF, CLKINT, and CLKDLY macros. The corner CCCs support CLKBUF, CLKINT, and CLKDLY.

Fusion

- AFS600 and AFS1500: All single-ended, differential, and voltage-referenced I/O standards (Pro I/O).
- AFS090 and AFS250: All single-ended and differential I/O standards.

Clock Sources for PLL and CLKDLY Macros

The input reference clock (CLKA for a PLL macro, CLK for a CLKDLY macro) can be accessed from different sources via the associated clock multiplexer tree. Each CCC has the option of choosing the source of the input clock from one of the following:

- · Hardwired I/O
- External I/O
- Core Logic
- RC Oscillator (Fusion only)
- Crystal Oscillator (Fusion only)

The SmartGen macro builder tool allows users to easily create the PLL and CLKDLY macros with the desired settings. Microsemi strongly recommends using SmartGen to generate the CCC macros.

Hardwired I/O Clock Source

Hardwired I/O refers to global input pins that are hardwired to the multiplexer tree, which directly accesses the CCC global buffers. These global input pins have designated pin locations and are indicated with the I/O naming convention *Gmn* (*m* refers to any one of the positions where the PLL core is available, and *n* refers to any one of the three global input MUXes and the pin number of the associated global location, *m*). Choosing this option provides the benefit of directly connecting to the CCC reference clock input, which provides less delay. See Figure 4-9 on page 90 for an example illustration of the connections, shown in red. If a CLKDLY macro is initiated to utilize the programmable delay element of the CCC, the clock input can be placed at one of nine dedicated global input pin locations. In other words, if Hardwired I/O is chosen as the input source, the user can decide to place the input pin in one of the GmA0, GmA1, GmA2, GmB0, GmB1, GmB2, GmC0, GmC1, or GmC2 locations of the low power flash devices. When a PLL macro is used to utilize the PLL core in a CCC location, the clock input of the PLL can only be connected to one of three GmA* global pin locations: GmA0, GmA1, or GmA2.

IGLOO and ProASIC3 CCC Locations

In all IGLOO and ProASIC3 devices (except 10 k through 30 k gate devices, which do not contain PLLs), six CCCs are located in the same positions as the IGLOOe and ProASIC3E CCCs. Only one of the CCCs has an integrated PLL and is located in the middle of the west (middle left) side of the device. The other five CCCs are simplified CCCs and are located in the four corners and the middle of the east side of the device (Figure 4-14).



Figure 4-14 • CCC Locations in IGLOO and ProASIC3 Family Devices (except 10 k through 30 k gate devices)

Note: The number and architecture of the banks are different for some devices.

10 k through 30 k gate devices do not support PLL features. In these devices, there are two CCC-GLs at the lower corners (one at the lower right, and one at the lower left). These CCC-GLs do not have programmable delays.



Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

```
wire VCC, GND;
VCC VCC_1_net(.Y(VCC));
GND GND_1_net(.Y(GND));
CLKDLY Inst1(.CLK(CLK), .GL(GL), .DLYGL0(VCC), .DLYGL1(GND), .DLYGL2(VCC),
.DLYGL3(GND), .DLYGL4(GND));
endmodule
```

Detailed Usage Information

Clock Frequency Synthesis

Deriving clocks of various frequencies from a single reference clock is known as frequency synthesis. The PLL has an input frequency range from 1.5 to 350 MHz. This frequency is automatically divided down to a range between 1.5 MHz and 5.5 MHz by input dividers (not shown in Figure 4-19 on page 100) between PLL macro inputs and PLL phase detector inputs. The VCO output is capable of an output range from 24 to 350 MHz. With dividers before the input to the PLL core and following the VCO outputs, the VCO output frequency can be divided to provide the final frequency range from 0.75 to 350 MHz. Using SmartGen, the dividers are automatically set to achieve the closest possible matches to the specified output frequencies.

Users should be cautious when selecting the desired PLL input and output frequencies and the I/O buffer standard used to connect to the PLL input and output clocks. Depending on the I/O standards used for the PLL input and output clocks, the I/O frequencies have different maximum limits. Refer to the family datasheets for specifications of maximum I/O frequencies for supported I/O standards. Desired PLL input or output frequencies will not be achieved if the selected frequencies are higher than the maximum I/O frequencies allowed by the selected I/O standards. Users should be careful when selecting the I/O standards used for PLL input and output clocks. Performing post-layout simulation can help detect this type of error, which will be identified with pulse width violation errors. Users are strongly encouraged to perform post-layout simulation to ensure the I/O standard used can provide the desired PLL input or output frequencies. Users can also choose to cascade PLLs together to achieve the high frequencies needed for their applications. Details of cascading PLLs are discussed in the "Cascading CCCs" section on page 125.

In SmartGen, the actual generated frequency (under typical operating conditions) will be displayed beside the requested output frequency value. This provides the ability to determine the exact frequency that can be generated by SmartGen, in real time. The log file generated by SmartGen is a useful tool in determining how closely the requested clock frequencies match the user specifications. For example, assume a user specifies 101 MHz as one of the secondary output frequencies. If the best output frequency that could be achieved were 100 MHz, the log file generated by SmartGen would indicate the actual generated frequency.

Simulation Verification

The integration of the generated PLL and CLKDLY modules is similar to any VHDL component or Verilog module instantiation in a larger design; i.e., there is no special requirement that users need to take into account to successfully synthesize their designs.

For simulation purposes, users need to refer to the VITAL or Verilog library that includes the functional description and associated timing parameters. Refer to the Software Tools section of the Microsemi SoC Products Group website to obtain the family simulation libraries. If Designer is installed, these libraries are stored in the following locations:

<Designer_Installation_Directory>\lib\vtl\95\proasic3.vhd

<Designer_Installation_Directory>Vib\vtl\95\proasic3e.vhd

- <Designer_Installation_Directory>\lib\vlog\proasic3.v
- <Designer_Installation_Directory>\lib\vlog\proasic3e.v

For Libero users, there is no need to compile the simulation libraries, as they are conveniently precompiled in the $ModelSim^{\mbox{\sc B}}$ Microsemi simulation tool.

6 – SRAM and FIFO Memories in Microsemi's Low Power Flash Devices

Introduction

As design complexity grows, greater demands are placed upon an FPGA's embedded memory. Fusion, IGLOO, and ProASIC3 devices provide the flexibility of true dual-port and two-port SRAM blocks. The embedded memory, along with built-in, dedicated FIFO control logic, can be used to create cascading RAM blocks and FIFOs without using additional logic gates.

IGLOO, IGLOO PLUS, and ProASIC3L FPGAs contain an additional feature that allows the device to be put in a low power mode called Flash*Freeze. In this mode, the core draws minimal power (on the order of 2 to 127 μ W) and still retains values on the embedded SRAM/FIFO and registers. Flash*Freeze technology allows the user to switch to Active mode on demand, thus simplifying power management and the use of SRAM/FIFOs.

Device Architecture

The low power flash devices feature up to 504 kbits of RAM in 4,608-bit blocks (Figure 6-1 on page 148 and Figure 6-2 on page 149). The total embedded SRAM for each device can be found in the datasheets. These memory blocks are arranged along the top and bottom of the device to allow better access from the core and I/O (in some devices, they are only available on the north side of the device). Every RAM block has a flexible, hardwired, embedded FIFO controller, enabling the user to implement efficient FIFOs without sacrificing user gates.

In the IGLOO and ProASIC3 families of devices, the following memories are supported:

- 30 k gate devices and smaller do not support SRAM and FIFO.
- 60 k and 125 k gate devices support memories on the north side of the device only.
- 250 k devices and larger support memories on the north and south sides of the device.

In Fusion devices, the following memories are supported:

- AFS090 and AFS250 support memories on the north side of the device only.
- AFS600 and AFS1500 support memories on the north and south sides of the device.

Advanced I/Os—IGLOO, ProASIC3L, and ProASIC3

Table 7-2 and Table 7-3 show the voltages and compatible I/O standards for the IGLOO, ProASIC3L, and ProASIC3 families.

I/Os provide programmable slew rates (except 30 K gate devices), drive strengths, and weak pull-up and pull-down circuits. 3.3 V PCI and 3.3 V PCI-X can be configured to be 5 V–tolerant. See the "5 V Input Tolerance" section on page 194 for possible implementations of 5 V tolerance.

All I/Os are in a known state during power-up, and any power-up sequence is allowed without current impact. Refer to the "I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)" section in the datasheet for more information. During power-up, before reaching activation levels, the I/O input and output buffers are disabled while the weak pull-up is enabled. Activation levels are described in the datasheet.

IGLOO	AGL015	AGL030	AGL060	AGL125	AGL250		AGL600	AGL1000
ProASIC3	A3P015	A3P030	A3P060	A3P125	A3P250/ A3P250L	A3P400	A3P600/ A3P600L	A3P1000/ A3P1000L
Single-Ended								
LVTTL/LVCMOS 3.3 V, LVCMOS 2.5 V / 1.8 V / 1.5 V / 1.2 V LVCMOS 2.5 V / 5.0 V	1	1	1	1	1	1	1	1
3.3 V PCI/PCI-X	-	-	1	1	1	1	1	1
Differential								
LVPECL, LVDS, B-LVDS, M-LVDS	_	_	_	_	1	1	1	1

Table 7-2 • Supported I/O Standards

I/O Banks and I/O Standards Compatibility

I/Os are grouped into I/O voltage banks.

Each I/O voltage bank has dedicated I/O supply and ground voltages (VMV/GNDQ for input buffers and VCCI/GND for output buffers). This isolation is necessary to minimize simultaneous switching noise from the input and output (SSI and SSO). The switching noise (ground bounce and power bounce) is generated by the output buffers and transferred into input buffer circuits, and vice versa. Because of these dedicated supplies, only I/Os with compatible standards can be assigned to the same I/O voltage bank. Table 7-3 shows the required voltage compatibility values for each of these voltages.

There are four I/O banks on the 250K gate through 1M gate devices.

There are two I/O banks on the 30K, 60K, and 125K gate devices.

I/O standards are compatible if their VCCI and VMV values are identical. VMV and GNDQ are "quiet" input power supply pins and are not used on 30K gate devices (Table 7-3).

Table 7-3 • VCCI Voltages and Compatible IGLOO and ProASIC3 Standards

VCCI and VMV (typical)	Compatible Standards
3.3 V	LVTTL/LVCMOS 3.3, PCI 3.3, PCI-X 3.3 LVPECL
2.5 V	LVCMOS 2.5, LVCMOS 2.5/5.0, LVDS, B-LVDS, M-LVDS
1.8 V	LVCMOS 1.8
1.5 V	LVCMOS 1.5
1.2 V	LVCMOS 1.2

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I/O Structures in IGLOO and ProASIC3 Devices

I/O Features

Low power flash devices support multiple I/O features that make board design easier. For example, an I/O feature like Schmitt Trigger in the ProASIC3E input buffer saves the board space that would be used by an external Schmitt trigger for a slow or noisy input signal. These features are also programmable for each I/O, which in turn gives flexibility in interfacing with other components. The following is a detailed description of all available features in low power flash devices.

I/O Programmable Features

Low power flash devices offer many flexible I/O features to support a wide variety of board designs. Some of the features are programmable, with a range for selection. Table 7-7 lists programmable I/O features and their ranges.

Feature ¹	Description	Range
Slew Control	Output slew rate	HIGH, LOW
Output Drive (mA)	Output drive strength	2, 4, 6, 8, 12, 16, 24
Skew Control	Output tristate enable delay option	ON, OFF
Resistor Pull	Resistor pull circuit	Up, Down, None
Input Delay ²	Input delay	OFF, 0–7
Schmitt Trigger	Schmitt trigger for input only	ON, OFF

Table 7-7 • Programmable I/O Features	(user control via I/O Attribute Editor)
---------------------------------------	---

Notes:

- 1. Limitations of these features with respect to different devices are discussed in later sections.
- 2. Programmable input delay is applicable only to ProASIC3EL and RT ProASIC3 devices.

Hot-Swap Support

A pull-up clamp diode must not be present in the I/O circuitry if the hot-swap feature is used. The 3.3 V PCI standard requires a pull-up clamp diode on the I/O, so it cannot be selected if hot-swap capability is required. The A3P030 device does not support 3.3 V PCI, so it is the only device in the ProASIC3 family that supports the hot-swap feature. All devices in the ProASIC3E family are hot-swappable. All standards except LVCMOS 2.5/5.0 V and 3.3 V PCI/PCI-X support the hot-swap feature.

The hot-swap feature appears as a read-only check box in the I/O Attribute Editor that shows whether an I/O is hot-swappable or not. Refer to the *"Power-Up/-Down Behavior of Low Power Flash Devices"* section on page 373 for details on hot-swapping.

Hot-swapping (also called hot-plugging) is the operation of hot insertion or hot removal of a card in a powered-up system. The levels of hot-swap support and examples of related applications are described in Table 7-8 on page 189 to Table 7-11 on page 190. The I/Os also need to be configured in hot-insertion mode if hot-plugging compliance is required. The AGL030 and A3P030 devices have an I/O structure that allows the support of Level 3 and Level 4 hot-swap with only two levels of staging.

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I/O Structures in IGLOOe and ProASIC3E Devices

IGLOOe and ProASIC3E devices support output slew rate control: high and low. Microsemi recommends the high slew rate option to minimize the propagation delay. This high-speed option may introduce noise into the system if appropriate signal integrity measures are not adopted. Selecting a low slew rate reduces this kind of noise but adds some delays in the system. Low slew rate is recommended when bus transients are expected.

Output Drive

The output buffers of IGLOOe and ProASIC3E devices can provide multiple drive strengths to meet signal integrity requirements. The LVTTL and LVCMOS (except 1.2 V LVCMOS) standards have selectable drive strengths. Other standards have a preset value.

Drive strength should also be selected according to the design requirements and noise immunity of the system.

The output slew rate and multiple drive strength controls are available in LVTTL/LVCMOS 3.3 V, LVCMOS 2.5 V, LVCMOS 2.5 V / 5.0 V input, LVCMOS 1.8 V, and LVCMOS 1.5 V. All other I/O standards have a high output slew rate by default.

For other IGLOOe and ProASIC3E devices, refer to Table 8-15 for more information about the slew rate and drive strength specification.

There will be a difference in timing between the Standard Plus I/O banks and the Advanced I/O banks. Refer to the I/O timing tables in the datasheet for the standards supported by each device.

I/O Standards	2 mA	4 mA	6 mA	8 mA	12 mA	16 mA	24 mA	Slew	
LVTTL/LVCMOS 3.3 V	1	1	1	~	~	1	~	High	Low
LVCMOS 2.5 V	~	1	1	1	~	1	~	High	Low
LVCMOS 2.5/5.0 V	1	1	1	~	~	1	~	High	Low
LVCMOS 1.8 V	1	1	1	1	1	1	-	High	Low
LVCMOS 1.5 V	1	1	1	~	1	-	_	High	Low

Table 8-15 • IGLOOe and ProASIC3E I/O Standards—Output Drive and Slew Rate



Programming Support in Flash Devices

The flash FPGAs listed in Table 11-1 support flash in-system programming and the functions described in this document.

Series	Family [*]	Description				
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology				
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards				
	IGLOO nano	The industry's lowest-power, smallest-size solution, supporting 1.2 V to 1.5 V core voltage with Flash*Freeze technology				
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities				
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs				
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards				
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities				
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V core voltage with Flash*Freeze technology				
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L				
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L				
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications				
SmartFusion	SmartFusion	Mixed-signal FPGA integrating FPGA fabric, programmable microcontroller subsystem (MSS), including programmable analog and ARM [®] Cortex™-M3 hard processor and flash memory in a monolithic device				
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM [®] Cortex™-M1 soft processors, and flash memory into a monolithic device				
ProASIC	ProASIC	First generation ProASIC devices				
	ProASIC ^{PLUS}	Second generation ProASIC devices				

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 11-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 11-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

Cortex-M1 Device Security

Cortex-M1-enabled devices are shipped with the following security features:

- FPGA array enabled for AES-encrypted programming and verification
- FlashROM enabled for AES-encrypted Write and Verify
- · Fusion Embedded Flash Memory enabled for AES-encrypted Write

AES Encryption of Programming Files

Low power flash devices employ AES as part of the security mechanism that prevents invasive and noninvasive attacks. The mechanism entails encrypting the programming file with AES encryption and then passing the programming file through the AES decryption core, which is embedded in the device. The file is decrypted there, and the device is successfully programmed. The AES master key is stored in on-chip nonvolatile memory (flash). The AES master key can be preloaded into parts in a secure programming environment (such as the Microsemi In-House Programming center), and then "blank" parts can be shipped to an untrusted programming or manufacturing center for final personalization with an AES-encrypted bitstream. Late-stage product changes or personalization can be implemented easily and securely by simply sending a STAPL file with AES-encrypted data. Secure remote field updates over public networks (such as the Internet) are possible by sending and programming a STAPL file with AES-encrypted data.

The AES key protects the programming data for file transfer into the device with 128-bit AES encryption. If AES encryption is used, the AES key is stored or preprogrammed into the device. To program, you must use an AES-encrypted file, and the encryption used on the file must match the encryption key already in the device.

The AES key is protected by a FlashLock security Pass Key that is also implemented in each device. The AES key is always protected by the FlashLock Key, and the AES-encrypted file does NOT contain the FlashLock Key. This FlashLock Pass Key technology is exclusive to the Microsemi flash-based device families. FlashLock Pass Key technology can also be implemented without the AES encryption option, providing a choice of different security levels.

In essence, security features can be categorized into the following three options:

- AES encryption with FlashLock Pass Key protection
- FlashLock protection only (no AES encryption)
- No protection

Each of the above options is explained in more detail in the following sections with application examples and software implementation options.

Advanced Encryption Standard

The 128-bit AES standard (FIPS-192) block cipher is the NIST (National Institute of Standards and Technology) replacement for DES (Data Encryption Standard FIPS46-2). AES has been designed to protect sensitive government information well into the 21st century. It replaces the aging DES, which NIST adopted in 1977 as a Federal Information Processing Standard used by federal agencies to protect sensitive, unclassified information. The 128-bit AES standard has 3.4×10^{38} possible 128-bit key variants, and it has been estimated that it would take 1,000 trillion years to crack 128-bit AES cipher text using exhaustive techniques. Keys are stored (securely) in low power flash devices in nonvolatile flash memory. All programming files sent to the device can be authenticated by the part prior to programming to ensure that bad programming data is not loaded into the part that may possibly damage it. All programming verification is performed on-chip, ensuring that the contents of low power flash devices remain secure.

Microsemi has implemented the 128-bit AES (Rijndael) algorithm in low power flash devices. With this key size, there are approximately 3.4×10^{38} possible 128-bit keys. DES has a 56-bit key size, which provides approximately 7.2×10^{16} possible keys. In their AES fact sheet, the National Institute of Standards and Technology uses the following hypothetical example to illustrate the theoretical security provided by AES. If one were to assume that a computing system existed that could recover a DES key in a second, it would take that same machine approximately 149 trillion years to crack a 128-bit AES key. NIST continues to make their point by stating the universe is believed to be less than 20 billion years old.¹

Programming Voltage (VPUMP) and VJTAG

Low-power flash devices support on-chip charge pumps, and therefore require only a single 3.3 V programming voltage for the VPUMP pin during programming. When the device is not being programmed, the VPUMP pin can be left floating or can be tied (pulled up) to any voltage between 0 V and 3.6 V². During programming, the target board or the FlashPro4/3/3X programmer can provide VPUMP. FlashPro4/3/3X is capable of supplying VPUMP to a single device. If more than one device is to be programmed using FlashPro4/3/3X on a given board, FlashPro4/3/3X should not be relied on to supply the VPUMP voltage. A FlashPro4/3/3X programmer is not capable of providing reliable VJTAG voltage. The board must supply VJTAG voltage to the device and the VJTAG pin of the programmer header must be connected to the device VJTAG pin. Microsemi recommends that VPUMP³ and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail. Refer to the "Board-Level Considerations" section on page 337 for capacitor requirements.

Low power flash device I/Os support a bank-based, voltage-supply architecture that simultaneously supports multiple I/O voltage standards (Table 13-2). By isolating the JTAG power supply in a separate bank from the user I/Os, low power flash devices provide greater flexibility with supply selection and simplify power supply and printed circuit board (PCB) design. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). Microsemi recommends that TCK be tied to GND through a 200 ohm to 1 Kohm resistor. This prevents a possible totempole current on the input buffer stage. For TDI, TMS, and TRST pins, the devices provide an internal nominal 10 Kohm pull-up resistor. During programming, all I/O pins, except for JTAG interface pins, are tristated and weakly pulled up to VCCI. This isolates the part and prevents the signals from floating. The JTAG interface pins are driven by the FlashPro4/3/3X during programming, including the TRST pin, which is driven HIGH.

Power Supply	Programming Mode	Current during Programming
VCC	1.2 V / 1.5 V	< 70 mA
VCCI	1.2 V / 1.5 V / 1.8 V / 2.5 V / 3.3 V (bank-selectable)	I/Os are weakly pulled up.
VJTAG	1.2 V / 1.5 V / 1.8 V / 2.5 V / 3.3 V	< 20 mA
VPUMP	3.15 V to 3.45 V	< 80 mA

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Note: All supply voltages should be at 1.5 V or higher, regardless of the setting during normal operation, except for IGLOO nano, where 1.2 V VCC and VJTAG programming is allowed.

Nonvolatile Memory (NVM) Programming Voltage

SmartFusion and Fusion devices need stable VCCNVM/VCCENVM³ (1.5 V power supply to the embedded nonvolatile memory blocks) and VCCOSC/VCCROSC⁴ (3.3 V power supply to the integrated RC oscillator). The tolerance of VCCNVM/VCCENVM is \pm 5% and VCCOSC/VCCROSC is \pm 5%.

Unstable supply voltage on these pins can cause an NVM programming failure due to NVM page corruption. The NVM page can also be corrupted if the NVM reset pin has noise. This signal must be tied off properly.

Microsemi recommends installing the following capacitors⁵ on the VCCNVM/VCCENVM and VCCOSC/VCCROSC pins:

- Add one bypass capacitor of 10 μF for each power supply plane followed by an array of decoupling capacitors of 0.1 $\mu F.$
- Add one 0.1 µF capacitor near each pin.

^{2.} During sleep mode in IGLOO devices connect VPUMP to GND.

VPUMP has to be quiet for successful programming. Therefore VPUMP must be separate and required capacitors must be installed close to the FPGA VPUMP pin.

^{4.} VCCROSC is for SmartFusion.

^{5.} The capacitors cannot guarantee reliable operation of the device if the board layout is not done properly.

List of Changes

Date	Changes	Page				
August 2012	This chapter will now be published standalone as an application note in addition to being part of the IGLOO/ProASIC3/Fusion FPGA fabric user's guides (SAR 38769).	N/A				
	The "ISP Programming Header Information" section was revised to update the description of FP3-10PIN-ADAPTER-KIT in Table 13-3 • Programming Header Ordering Codes, clarifying that it is the adapter kit used for ProASIC ^{PLUS} based boards, and also for ProASIC3 based boards where a compact programming header is being used (SAR 36779).	335				
June 2011	The VPUMP programming mode voltage was corrected in Table 13-2 • Power Supplies. The correct value is 3.15 V to 3.45 V (SAR 30668).	329				
	The notes associated with Figure 13-5 • Programming Header (top view) and Figure 13-6 • Board Layout and Programming Header Top View were revised to make clear the fact that IGLOO nano V2 devices can be programmed at 1.2 V (SAR 30787).					
	Figure 13-6 • Board Layout and Programming Header Top View was revised to include resistors tying TCK and TRST to GND. Microsemi recommends tying off TCK and TRST to GND if JTAG is not used (SAR 22921). RT ProASIC3 was added to the list of device families.	337				
	In the "ISP Programming Header Information" section, the kit for adapting ProASIC ^{PLUS} devices was changed from FP3-10PIN-ADAPTER-KIT to FP3-26PIN-ADAPTER-KIT (SAR 20878).	335				
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.					
	References to FlashPro4 and FlashPro3X were added to this chapter, giving distinctions between them. References to SmartGen were deleted and replaced with Libero IDE Catalog.					
	The "ISP Architecture" section was revised to indicate that V2 devices can be programmed at 1.2 V VCC with FlashPro4.	327				
	SmartFusion was added to Table 13-1 • Flash-Based FPGAs Supporting ISP.	328				
	The "Programming Voltage (VPUMP) and VJTAG" section was revised and 1.2 V was added to Table 13-2 • Power Supplies.	329				
	The "Nonvolatile Memory (NVM) Programming Voltage" section is new.	329				
	Cortex-M3 was added to the "Cortex-M1 and Cortex-M3 Device Security" section.	331				
	In the "ISP Programming Header Information" section, the additional header adapter ordering number was changed from FP3-26PIN-ADAPTER to FP3-10PIN-ADAPTER-KIT, which contains 26-pin migration capability.	335				
	The description of NC was updated in Figure 13-5 • Programming Header (top view), Table 13-4 • Programming Header Pin Numbers and Description and Figure 13-6 • Board Layout and Programming Header Top View.	335, 336				
	The "Symptoms of a Signal Integrity Problem" section was revised to add that customers are expected to troubleshoot board-level signal integrity issues by measuring voltages and taking scope plots. "FlashPro4/3/3X allows TCK to be lowered from 6 MHz down to 1 MHz to allow you to address some signal integrity problems" formerly read, "from 24 MHz down to 1 MHz." "The Scan Chain command expects to see 0x2" was changed to 0x1.	337				

The following table lists critical changes that were made in each revision of the chapter.



useless to the thief. To learn more about the low power flash devices' security features, refer to the "Security in Low Power Flash Devices" section on page 301.

Figure 15-5 • ProASIC3 Device Encryption Flow

Conclusion

The Fusion, IGLOO, and ProASIC3 FPGAs are ideal for applications that require field upgrades. The single-chip devices save board space by eliminating the need for EEPROM. The built-in AES with MAC enables transmission of programming data over any network without fear of design theft. Fusion, IGLOO, and ProASIC3 FPGAs are IEEE 1532–compliant and support STAPL, making the target programming software easy to implement.

Microsemi

Microprocessor Programming of Microsemi's Low Power Flash Devices

List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
September 2012	The "Security" section was modified to clarify that Microsemi does not support read-back of FPGA core-programmed data (SAR 41235).	354
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	
v1.4 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to Table 15-1 • Flash-Based FPGAs.	350
v1.3 (October 2008)	The "Microprocessor Programming Support in Flash Devices" section was revised to include new families and make the information more concise.	350
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 15-1 • Flash-Based FPGAs:	350
	 ProASIC3L was updated to include 1.5 V. 	
	The number of PLLs for ProASIC3E was changed from five to six.	
v1.1 (March 2008)	The "Microprocessor Programming Support in Flash Devices" section was updated to include information on the IGLOO PLUS family. The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	350

18 – Power-Up/-Down Behavior of Low Power Flash Devices

Introduction

Microsemi's low power flash devices are flash-based FPGAs manufactured on a 0.13 μ m process node. These devices offer a single-chip, reprogrammable solution and support Level 0 live at power-up (LAPU) due to their nonvolatile architecture.

Microsemi's low power flash FPGA families are optimized for logic area, I/O features, and performance. IGLOO[®] devices are optimized for power, making them the industry's lowest power programmable solution. IGLOO PLUS FPGAs offer enhanced I/O features beyond those of the IGLOO ultra-low power solution for I/O-intensive low power applications. IGLOO nano devices are the industry's lowest-power cost-effective solution. ProASIC3[®]L FPGAs balance low power with high performance. The ProASIC3 family is Microsemi's high-performance flash FPGA solution. ProASIC3 nano devices offer the lowest-cost solution with enhanced I/O capabilities.

Microsemi's low power flash devices exhibit very low transient current on each power supply during power-up. The peak value of the transient current depends on the device size, temperature, voltage levels, and power-up sequence.

The following devices can have inputs driven in while the device is not powered:

- IGLOO (AGL015 and AGL030)
- IGLOO nano (all devices)
- IGLOO PLUS (AGLP030, AGLP060, AGLP125)
- IGLOOe (AGLE600, AGLE3000)
- ProASIC3L (A3PE3000L)
- ProASIC3 (A3P015, A3P030)
- ProASIC3 nano (all devices)
- ProASIC3E (A3PE600, A3PE1500, A3PE3000)
- Military ProASIC3EL (A3PE600L, A3PE3000L, but not A3P1000)
- RT ProASIC3 (RT3PE600L, RT3PE3000L)

The driven I/Os do not pull up power planes, and the current draw is limited to very small leakage current, making them suitable for applications that require cold-sparing. These devices are hot-swappable, meaning they can be inserted in a live power system.¹

^{1.} For more details on the levels of hot-swap compatibility in Microsemi's low power flash devices, refer to the "Hot-Swap Support" section in the I/O Structures chapter of the FPGA fabric user's guide for the device you are using.

Power-Up/-Down Behavior of Low Power Flash Devices

Figure 18-3 • I/O State when VCCI Is Powered before VCC

Power-Up to Functional Time

At power-up, device I/Os exit the tristate mode and become functional once the last voltage supply in the power-up sequence (VCCI or VCC) reaches its functional activation level. The power-up–to–functional time is the time it takes for the last supply to power up from zero to its functional level. Note that the functional level of the power supply during power-up may vary slightly within the specification at different ramp-rates. Refer to Table 18-2 for the functional level of the voltage supplies at power-up.

Typical I/O behavior during power-up-to-functional time is illustrated in Figure 18-2 on page 377 and Figure 18-3.

Device	VCC Functional Activation Level (V)	VCCI Functional Activation Level (V)
ProASIC3, ProASIC3 nano, IGLOO, IGLOO nano, IGLOO PLUS, and ProASIC3L devices running at VCC = 1.5 V*	0.85 V ± 0.25 V	0.9 V ± 0.3 V
IGLOO, IGLOO nano, IGLOO PLUS, and ProASIC3L devices running at VCC = 1.2 V*	0.85 V ± 0.2 V	0.9 V ± 0.15 V

Table 18-2 • Power-Up Functional Activation Levels for VCC and VCCI

Note: *V5 devices will require a 1.5 V VCC supply, whereas V2 devices can utilize either a 1.2 V or 1.5 V VCC.

Microsemi's low power flash devices meet Level 0 LAPU; that is, they can be functional prior to V_{CC} reaching the regulated voltage required. This important advantage distinguishes low power flash devices from their SRAM-based counterparts. SRAM-based FPGAs, due to their volatile technology, require hundreds of milliseconds after power-up to configure the design bitstream before they become functional. Refer to Figure 18-4 on page 379 and Figure 18-5 on page 380 for more information.



Figure 18-4 • I/O State as a Function of VCCI and VCC Voltage Levels for IGLOO V5, IGLOO nano V5, IGLOO PLUS V5, ProASIC3L, and ProASIC3 Devices Running at VCC = 1.5 V ± 0.075 V

A – Summary of Changes

History of Revision to Chapters

The following table lists chapters that were affected in each revision of this document. Each chapter includes its own change history because it may appear in other device family user's guides. Refer to the individual chapter for a list of specific changes.

Revision (month/year)	Chapter Affected	List of Changes (page number)
Revision 4 (September 2012)	"Microprocessor Programming of Microsemi's Low Power Flash Devices" was revised.	356
Revision 3 (August 2012)	"FPGA Array Architecture in Low Power Flash Devices" was revised.	20
	"Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" was revised.	129
	"SRAM and FIFO Memories in Microsemi's Low Power Flash Devices" was revised.	173
	"I/O Structures in IGLOO and ProASIC3 Devices" was revised.	210
	"I/O Structures in IGLOOe and ProASIC3E Devices" was revised.	249
	The "Pin Descriptions" and "Packaging" chapters were removed. This information is now published in the datasheet for each product line (SAR 34773).	
	"In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X" was revised.	339
	"Boundary Scan in Low Power Flash Devices" was revised.	362
Revision 2 (December 2011)	"Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" was revised.	129
	"UJTAG Applications in Microsemi's Low Power Flash Devices" was revised.	372
Revision 1 (June 2011)	"Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" was revised.	129
	"I/O Structures in IGLOO and ProASIC3 Devices" was revised.	210
	"I/O Structures in IGLOOe and ProASIC3E Devices" was revised.	249
	"I/O Software Control in Low Power Flash Devices" was revised.	270
	"In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X" was revised.	339
Revision 0 (July 2010)	The ProASIC3L Flash Family FPGAs Handbook was divided into two parts to create the ProASIC3L Low Power Flash FPGAs Datasheet and the ProASIC3L FPGA Fabric User's Guide.	N/A
	"Global Resources in Low Power Flash Devices" was revised.	75
	"Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" was revised.	129
	"I/O Software Control in Low Power Flash Devices" was revised.	270



Summary of Changes

Revision (month/year)	Chapter Affected	List of Changes (page number)
Revision 0	"DDR for Microsemi's Low Power Flash Devices" was revised.	285
(continued)	"Programming Flash Devices" was revised.	298
	"In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X" was revised.	339
	"Core Voltage Switching Circuit for IGLOO and ProASIC3L In-System Programming" was revised.	347
	"Boundary Scan in Low Power Flash Devices" was revised.	362